

## GMBTA64

PNP SILICON TRANSISTOR

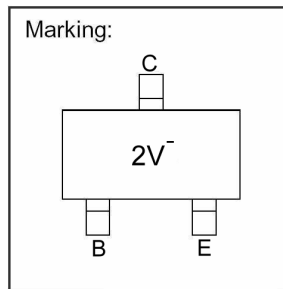
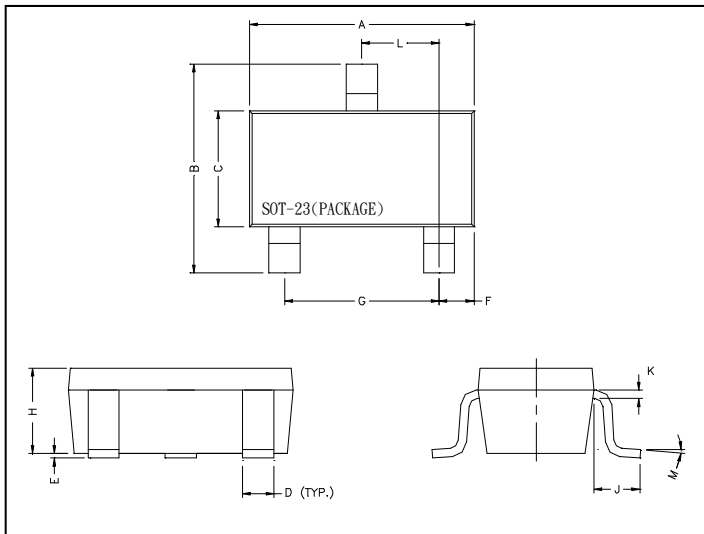
### Description

The GMBTA64 is designed for application requiring extremely high current gain at collector current to 500mA.

### Features

- High D.C. Current Gain
- For Complementary with NPN Type GMBTA14

### Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

### Absolute Maximum Ratings at Ta = 25°C

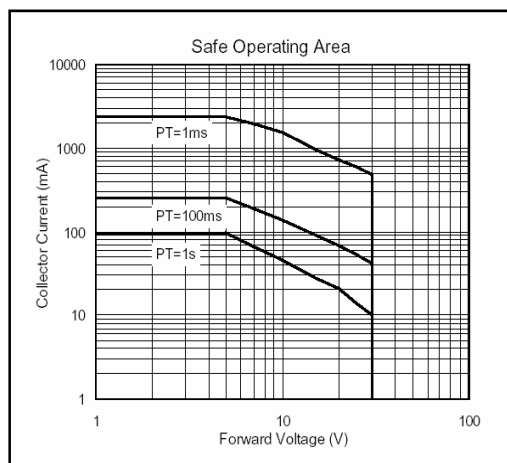
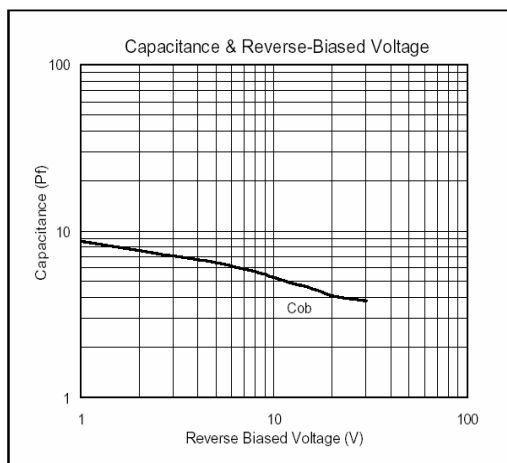
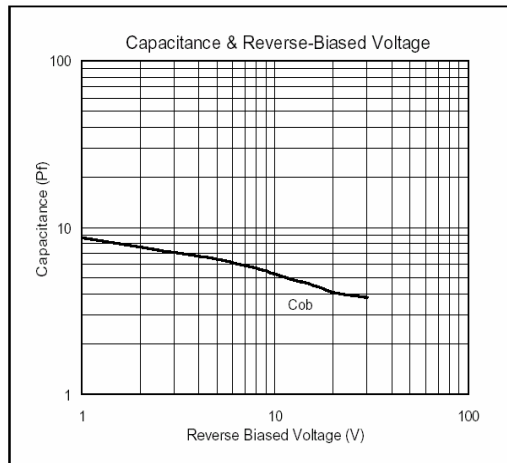
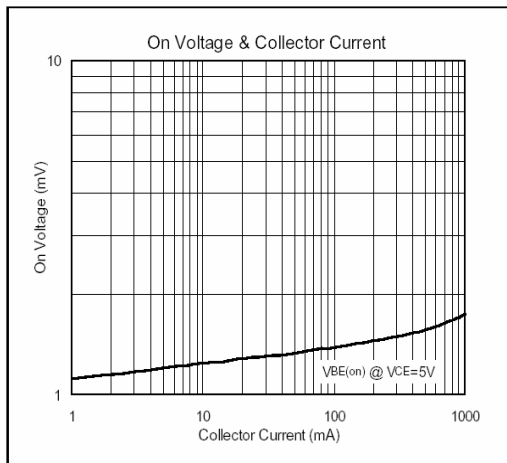
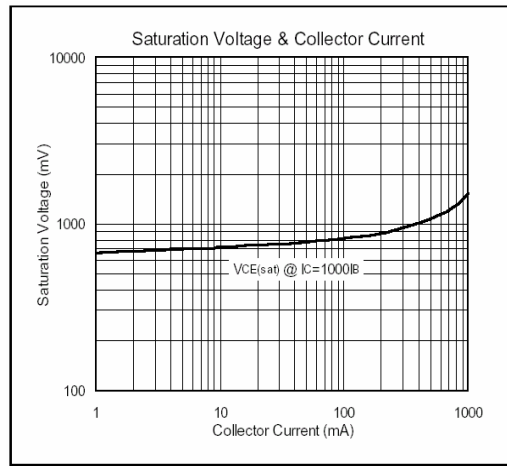
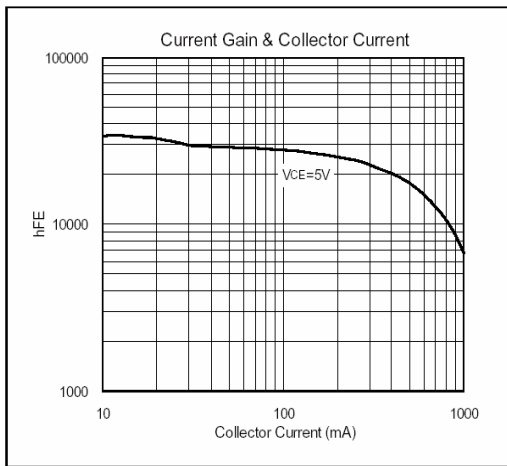
Parameter	Symbol	Ratings	Unit
Junction Temperature	T <sub>j</sub>	+150	°C
Storage Temperature	T <sub>stg</sub>	-55 ~ +150	°C
Collector to Base Voltage	V <sub>CB0</sub>	-30	V
Collector to Emitter Voltage	V <sub>CE0</sub>	-30	V
Emitter to Base Voltage	V <sub>EB0</sub>	-10	V
Collector Current	I <sub>C</sub>	-500	mA
Total Power Dissipation	P <sub>D</sub>	225	mW

### Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CB0</sub>	-30	-	-	V	I <sub>C</sub> =-100uA, I <sub>E</sub> =0
BV <sub>CE0</sub>	-30	-	-	V	I <sub>C</sub> =-100uA, I <sub>B</sub> =0
BV <sub>EB0</sub>	-10	-	-	V	I <sub>E</sub> =-10uA, I <sub>C</sub> =0
I <sub>CB0</sub>	-	-	-100	nA	V <sub>CB</sub> =-30V, I <sub>E</sub> =0
I <sub>EB0</sub>	-	-	-100	nA	V <sub>CE</sub> =-10V
V <sub>CE(sat)</sub>	-	-	-1.5	V	I <sub>C</sub> =-100mA, I <sub>B</sub> =-0.1mA
V <sub>BE(on)</sub>	-	-	-2	V	V <sub>CE</sub> =-5V, I <sub>C</sub> =-100mA
HFE1	10K	-	-		V <sub>CE</sub> =-5V, I <sub>C</sub> =-10mA
HFE2	20K	-	-		V <sub>CE</sub> =-5V, I <sub>C</sub> =-100mA
f <sub>T</sub>	125	-	-	MHz	V <sub>CE</sub> =-5V, I <sub>C</sub> =-100mA, f=100MHz

\*Pulse Test :Pulse width ≤380us,Duty Cycly≤2%

## Characteristics Curve



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